

Mirhasan Seyitsoy

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6744344/publications.pdf>

Version: 2024-02-01

40
papers

365
citations

759233

12
h-index

888059

17
g-index

41
all docs

41
docs citations

41
times ranked

147
citing authors

#	ARTICLE	IF	CITATIONS
1	A Study of Thermoelectric Performance of TlGaSe ₂ Layered Dichalcogenides from First-Principles Calculations: Vacancy Defects Modeling and Engineering. Physica Status Solidi (B): Basic Research, 2022, 259, 2100409.	1.5	3
2	Synthesis and magnetic characterizations of $Tl_{1-x}Mn_xGaSe_2$ layered semiconductor. Materials Research Express, 2020, 7, 085914.	2.3	3
3	Investigation of Basic Optical Properties of Tissue Phantoms Under 635 nm Low-Level Laser Irradiation. Optics Express, 2020, 28, 36511-36520.		2
4	Mott barrier behavior of metal/TlGaSe ₂ layered semiconductor junction. Semiconductor Science and Technology, 2020, 35, 125010.	2.0	5
5	Influence of native structural defects activated by illumination and under the memory effect conditions on ultrasonic wave propagation in TlInS ₂ ferroelectric semiconductor with incommensurate phase. Materials Research Express, 2019, 6, 085914.	1.6	1
6	Identification of Mn dopant in the structure of TlInS ₂ layered semiconductor. Materials Research Express, 2019, 6, 056110.	1.6	3
7	Magnetic resonance and magnetization studies of Fe implanted TlInS ₂ and TlGaSe ₂ crystals. Materials Research Express, 2019, 6, 076109.	1.6	3
8	Synthesis, Powder X-Ray Diffraction, and Ab Initio Study of TlInSe ₂ : Analysis of Its Thermoelectric Properties. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800835.	1.8	1
9	Diode Polarization and Resistive Switching in Metal/TlGaSe ₂ Semiconductor/Metal Devices. Semiconductors, 2018, 52, 2007-2016.	0.5	5
10	Origin of the optical absorption of TlGaSe ₂ layered semiconductor in the visible range. Semiconductor Science and Technology, 2018, 33, 075019.	2.0	10
11	Preparation, structure analysis and dielectric characteristics of the novel ferroelectric ceramics (1-x)Tl _{1-x} ETQq ₁ 1.0.784314 rgBT / Over structure. Journal of Alloys and Compounds, 2017, 711, 169-183.	5.5	4
12	Polarization switching in undoped and La-doped TlInS ₂ ferroelectric-semiconductors. Physica B: Condensed Matter, 2017, 526, 45-53.	2.7	5
13	Effect of deep native defects on ultrasound propagation in TlInS ₂ layered crystal. Physica B: Condensed Matter, 2016, 497, 86-92.	2.7	6
14	Identification of intrinsic deep level defects responsible for electret behavior in TlGaSe ₂ layered semiconductor. Physica B: Condensed Matter, 2016, 483, 82-89.	2.7	13
15	Enhancing the photoresponse of a TlGaSe ₂ semiconductor for ultraviolet detection applications. Physica Scripta, 2015, 90, 015805.	2.5	6
16	Characterization of deep level defects and thermally stimulated depolarization phenomena in La-doped TlInS ₂ layered semiconductor. Journal of Applied Physics, 2015, 117, .	2.5	13
17	Photoelectric activity of defects in La-doped layered TlInS ₂ crystals. Low Temperature Physics, 2014, 40, 830-836.	0.6	7
18	Field induced rectification and memristive behavior of TlGaSe ₂ layered semiconductor. Applied Physics Letters, 2014, 105, 152106.	3.3	4

#	ARTICLE	IF	CITATIONS
19	Preillumination induced change of electronic transport properties of TlGaSe ₂ semiconductor. Solid State Sciences, 2014, 33, 49-52.	3.2	3
20	Imprint electric field controlled electronic transport in TlGaSe ₂ crystals. Journal of Applied Physics, 2013, 114, 093706.	2.5	11
21	Phase transition sensitive to interlayer defects in layered semiconductor TlGaSe ₂ . Solid State Sciences, 2012, 14, 311-316.	3.2	8
22	Memory effect and new polarized state in the incommensurate phase of TlGaSe ₂ ferroelectric semiconductor. Journal of Applied Physics, 2011, 110, 013529.	2.5	11
23	Photoinduced Current Transient Spectroscopy of TlInS ₂ Layered Crystals Doped with Er, B, and Tb Impurities. Japanese Journal of Applied Physics, 2011, 50, 05FC08.	1.5	4
24	Origin of structural instability in TlInS ₂ (1-x)Se _{2x} solid solutions. Physica Scripta, 2011, 84, 015601.	2.5	14
25	The Role of Electronic Subsystem in the Negative Thermal Expansion of Ferroelectric Semiconductor TlGaSe ₂ . Japanese Journal of Applied Physics, 2011, 50, 05FD06.	1.5	5
26	Charged Defects as an Origin of the Memory Effect in Incommensurate Phase of TlInS ₂ Ferroelectric Semiconductors. Japanese Journal of Applied Physics, 2011, 50, 05FD07.	1.5	2
27	Activated impurity states in the incommensurate phase of ferroelectric semiconductor TlInS ₂ . Journal of Applied Physics, 2010, 108, 024111.	2.5	4
28	Charge disproportionation in TlGaSe ₂ crystals detected by dielectric spectroscopy. Journal of Applied Physics, 2010, 108, 074114.	2.5	8
29	Negative thermal expansion due to negative area compressibility in TlGaSe ₂ semiconductor with layered crystalline structure. Journal of Applied Physics, 2010, 108, 063540.	2.5	37
30	Thermal expansion and memory effect in the ferroelectric-semiconductor TlGaSe ₂ . Journal of Applied Physics, 2009, 106, 023532.	2.5	12
31	Temperature-dependent polarity reversal in Au/TlGaSe ₂ Schottky junctions. Journal of Applied Physics, 2009, 105, 043710.	2.5	6
32	Effect of electric field on negative linear expansion of ferroelectric-semiconductor TlGaSe ₂ . Journal of Applied Physics, 2009, 106, 063529.	2.5	9
33	Effect of illumination on negative linear expansion of TlGaSe ₂ layered crystals. Journal of Physics and Chemistry of Solids, 2008, 69, 2544-2547.	4.0	13
34	Electric field instabilities in TlGaSe ₂ crystals. Solid State Sciences, 2008, 10, 1666-1670.	3.2	13
35	Dielectric spectroscopy and nonequilibrium phase transitions in TlGaSe ₂ layered crystals. Semiconductor Science and Technology, 2007, 22, 843-850.	2.0	18
36	Mechanisms of current flow in p-TlGaSe ₂ single crystals. Semiconductor Science and Technology, 2006, 21, 1633-1638.	2.0	15

#	ARTICLE	IF	CITATIONS
37	The effect of thermal annealing on impurity states in ferroelectric- semiconductor TlGaSe ₂ within the incommensurate phase. <i>Semiconductor Science and Technology</i> , 2006, 21, 171-174.	2.0	23
38	Electret states and current oscillations in the ferroelectric semiconductor TlGaSe ₂ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 3781-3787.	1.8	18
39	Preparation, crystal structure, and electrical properties of thallium monosulfide in the vicinity of high-temperature phase transitions. <i>Physics of the Solid State</i> , 2006, 48, 2322-2327.	0.6	9
40	The effect of impurities on the phase transitions in the ferroelectric semiconductors TlInS ₂ and TlGaSe ₂ . <i>Journal of Physics Condensed Matter</i> , 2005, 17, 1985-1993.	1.8	28